

Transistors

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	–	–	10	μA	V _{GS} =12V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR) DSS}	45	–	–	V	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	–	–	1	μA	V _{DS} = 45V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	0.5	–	1.5	V	V _{DS} = 10V, I _D = 1mA
Static drain-source on-state resistance	R _{DS (on)} *	–	130	180	mΩ	I _D = 2.0A, V _{GS} = 4.5V
		–	135	190	mΩ	I _D = 2.0A, V _{GS} = 4V
		–	180	250	mΩ	I _D = 2.0A, V _{GS} = 2.5V
Forward transfer admittance	Y _{fs} *	1.5	–	–	S	V _{DS} = 10V, I _D = 2.0A
Input capacitance	C _{iss}	–	200	–	pF	V _{DS} = 10V
Output capacitance	C _{oss}	–	45	–	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	–	25	–	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	–	11	–	ns	V _{DD} ≐25V
Rise time	t _r *	–	16	–	ns	I _D = 1.0A
Turn-off delay time	t _{d (off)} *	–	21	–	ns	V _{GS} = 4.5V
Fall time	t _f *	–	11	–	ns	R _L =25Ω
Total gate charge	Q _g *	–	2.9	4.1	nC	V _{DD} ≐25V V _{GS} = 4.5V
Gate-source charge	Q _{gs} *	–	0.7	–	nC	I _D = 2.0A
Gate-drain charge	Q _{gd} *	–	0.9	–	nC	R _L =12.5Ω R _G =10Ω

*Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _{SD}	–	–	1.2	V	I _S = 0.8A, V _{GS} =0V

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